

RoHS

COMPLIANT

Phase Control Thyristors (Stud Version), 230 A



PRIMARY CHARACTERISTICS				
I _{T(AV)}	230 A			
V_{DRM}/V_{RRM}	1400 V, 1600 V			
V_{TM}	1.55 V			
I _{GT}	150 mA			
T_J	-40 °C to +125 °C			
Package	TO-93 (TO-209AB)			
Circuit configuration	Single SCR			

FEATURES

- · Center amplifying gate
- International standard case TO-93 (TO-209AB)
- Hermetic metal case with ceramic insulator
- Compression bonded encapsulation for heavy duty operations such as severe thermal cycling
- · Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

TYPICAL APPLICATIONS

- · DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
1		230	Α		
I _{T(AV)}	T _C	85	°C		
I _{T(RMS)}		360	Α		
	50 Hz	5700	^		
ITSM	60 Hz	5970	A A		
121	50 Hz	163	kA ² s		
I ² t	60 Hz	149	KA-S		
V _{DRM} /V _{RRM}		1400 to 1600	V		
t _q	Typical	100	μs		
T _J		-40 to +125	°C		

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	$\begin{split} I_{DRM}/I_{RRM} & \text{MAXIMUM AT} \\ T_J = T_J & \text{MAXIMUM} \\ & \text{mA} \end{split}$				
VS-ST230S	14	1400	1500	30				
V3-312303	16	1600	1700	30				



ABSOLUTE MAXIMUM RATINGS	S					
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum average on-state current	I _{T(AV)}	180° conduction, half sine wave			230	A °C
at case temperature					85	30
Maximum RMS on-state current	I _{T(RMS)}	DC at 78 °C	case temperat	ure	360	
		t = 10 ms	No voltage		5700	
Maximum peak, one-cycle	ı	t = 8.3 ms	reapplied		5970	A
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}		4800	
		t = 8.3 ms	reapplied	Sinusoidal half wave, initial $T_J = T_J$ maximum	5000	
	l ² t	t = 10 ms	No voltage		163	- kA ² s
Maximum I ² t for fusing		t = 8.3 ms	reapplied		148	
		t = 10 ms	100 % V _{RRM}		115	
		t = 8.3 ms	reapplied		105	
Maximum I ² √t for fusing	I²√t	t = 0.1 to 10	t = 0.1 to 10 ms, no voltage reapplied		1630	kA²√s
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	I _{T(AV)}), T _J = T _J maximum	0.92	V
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			V
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π	$(16.7 \% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			m 0
High level value of on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			0.81	mΩ
Maximum on-state voltage	V _{TM}	$I_{pk} = 720 \text{ A}, T_J = T_J \text{ maximum}, t_p = 10 \text{ ms sine pulse}$			1.55	V
Maximum holding current	I _H	T _ 05 °C	anada ayanlı 1	2.V registive lead	600	mΛ
Maximum (typical) latching current	ΙL	T _J = 25 °C, anode supply 12 V resistive load		1000 (300)	mA	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 Ω , $t_r \le 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$	1000	A/µs
Typical delay time	t _d	Gate current 1 A, $dl_g/dt = 1$ A/ μ s $V_d = 0.67 \% V_{DRM}$, $T_J = 25 °C$	1.0	
Typical turn-off time	t _q	$\begin{array}{l} I_{TM}=300~A,~T_J=T_J~maximum,~dI_F/dt=20~A/\mu s,\\ V_R=50~V,~dV/dt=20~V/\mu s,~gate~0~V~100~\Omega,~t_p=500~\mu s \end{array}$	100	μs

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	T _J = T _J maximum linear to 80 % rated V _{DRM}	500	V/µs
Maximum peak reverse and off-state leakage current	I _{RRM} , I _{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	30	mA



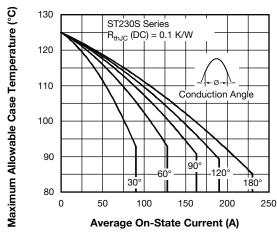
TRIGGERING						
DADAMETED	CVMPOL	TEGT COMPITIONS		VALUES		LINUTO
PARAMETER	SYMBOL	' '	EST CONDITIONS	TYP.	MAX.	UNITS
Maximum peak gate power	P _{GM}	$T_J = T_J$ maximum,	$t_p \leq 5 \; ms$	10.0		W
Maximum average gate power	P _{G(AV)}	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	2	.0	VV
Maximum peak positive gate current	I _{GM}	$T_J = T_J$ maximum,	$t_p \leq 5 \ ms$	3	.0	Α
Maximum peak positive gate voltage	+ V _{GM}	$T_J = T_J$ maximum, $t_p \le 5$ ms		s 20 5.0		V
Maximum peak negative gate voltage	- V _{GM}					
	I _{GT}	T _J = - 40 °C		180	-	
DC gate current required to trigger		T _J = 25 °C	Maximum required gate trigger/	90	150	mA
		T _J = 125 °C	current/voltage are the lowest value which will trigger all units 12 V anode to cathode applied	40	-	
		T _J = - 40 °C		2.9	-	
DC gate voltage required to trigger	V_{GT}	T _J = 25 °C		1.8	3.0	V
		T _J = 125 °C		1.2	-	1
DC gate current not to trigger	I _{GD}		Maximum gate current/voltage not	10		mA
DC gate voltage not to trigger	V _{GD}	$T_J = T_J \text{maximum} \text{to trigger is the maximum value} \\ \text{which will not trigger any unit with} \\ \text{rated} V_{DRM} \text{anode to cathode} \\ \text{applied}$		0.	25	V

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum operating junction temperature range	TJ		-40 to 125	°C	
Maximum storage temperature range	T _{Stg}		-40 to 150		
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	0.10	12.001	
Maximum thermal resistance, case to heatsink	R _{thC-hs}	Mounting surface, smooth, flat and greased	0.04	- K/W	
Mounting torque + 10.0/		Non-lubricated threads	31 (275)	N·m	
Mounting torque, ± 10 %		Lubricated threads	24.5 (210)	(lbf ⋅ in)	
Approximate weight			280	g	
Case style		See dimensions - link at the end of datasheet	TO-93 (TO-209AB)		

∆R _{thJC} CONDUCTION	ON			
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.016	0.012		
120°	0.019	0.020		
90°	0.025	0.027	$T_J = T_J$ maximum	K/W
60°	0.036	0.037		
30°	0.060	0.060		

Note

• The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC





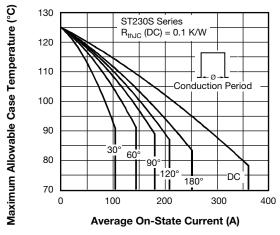


Fig. 2 - Current Ratings Characteristics

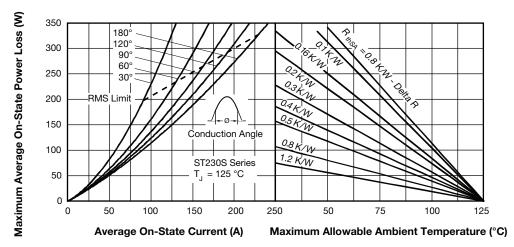


Fig. 3 - On-State Power Loss Characteristics

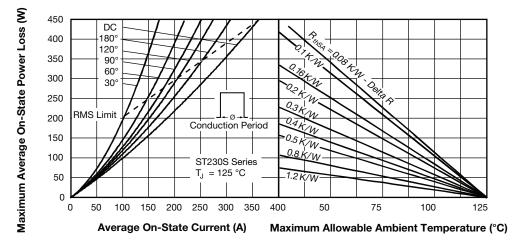


Fig. 4 - On-State Power Loss Characteristics

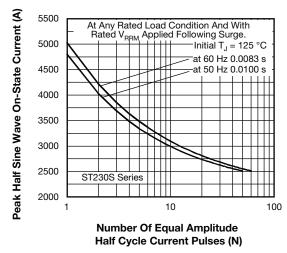


Fig. 5 - Maximum Non-Repetitive Surge Current

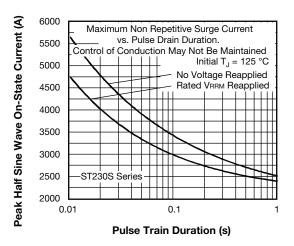


Fig. 6 - Maximum Non-Repetitive Surge Current

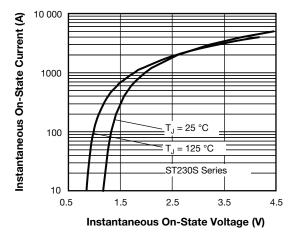


Fig. 7 - On-State Voltage Drop Characteristics

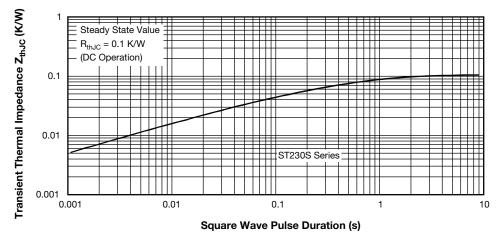


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

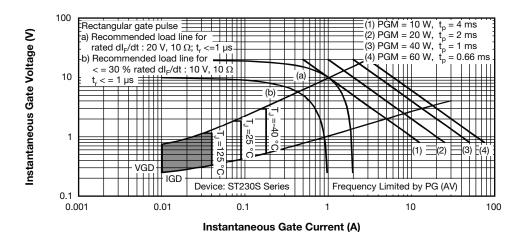
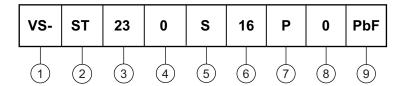


Fig. 9 - Gate Characteristics

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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Thyristor

- Essential part number

- 0 = converter grade

5 - S = compression bonding stud

6 - Voltage code x 100 = V_{RRM} (see Voltage Ratings table)

P = stud base 3/4"-16UNF2A threads

8 - 0 = eyelet terminals (gate and auxiliary cathode leads)

1 = fast-on terminals (gate and auxiliary cathode leads)

9 - None = standard production

- PbF = lead (Pb)-free

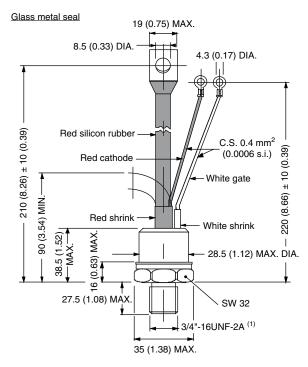
Note: For metric device M16 x 1.5 contact factory

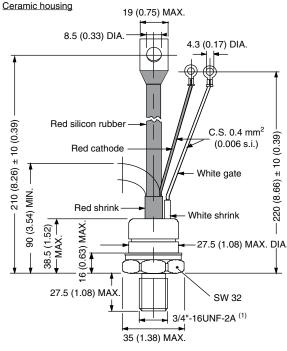
LINKS TO RELAT	ED DOCUMENTS
Dimensions	www.vishay.com/doc?95082

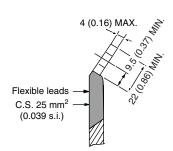


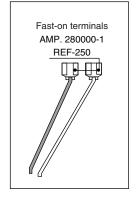
TO-209AB (TO-93)

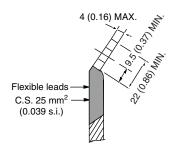
DIMENSIONS in millimeters (inches)











Note

(1) For metric device: M16 x 1.5 - length 21 (0.83) maximum



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